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Lu et al.(10) **Pub. No.: US 2024/0213264 A1**(43) **Pub. Date: Jun. 27, 2024**(54) **ACTIVE DEVICE SUBSTRATE**(71) Applicant: **AUO Corporation**, Hsinchu (TW)(72) Inventors: **Chia-Yang Lu**, Hsinchu (TW); **Pei-Yun Wang**, Hsinchu (TW)(73) Assignee: **AUO Corporation**, Hsinchu (TW)(21) Appl. No.: **18/091,383**(22) Filed: **Dec. 30, 2022**(30) **Foreign Application Priority Data**

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ABSTRACT

An active device substrate including a substrate, a transfer wire, a first insulating layer, a second insulating layer, a first semiconductor pattern, a second semiconductor pattern, a first connection structure, a second connection structure, a first gate, a second gate, a third insulating layer, a first source/drain, and a second source/drain is provided. The first insulating layer is located above the transfer wire. The second insulating layer is located above the first insulating layer. The first semiconductor pattern and the second semiconductor pattern are located between the first insulating layer and the second insulating layer. The first connection structure and the second connection structure are located above the second insulating layer and electrically connected to the transfer wire. The first gate and the second gate respectively overlap the first semiconductor pattern and the second semiconductor pattern.

